

CURRENTLY PENDING CLAIMS

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ALG
2/7/05

Please amend the claims as follows:

1.-8. (Cancelled)

9. (Currently Amended) A method for chemical mechanical polishing of tungsten comprising:

providing a semiconductor substrate comprising on one face tungsten and a dielectric material;

providing a chemical mechanical polishing composition comprising between about 0.5% and about 10% periodic acid, between about 0.1% and about 10% of a secondary oxidizer, and a pH adjusting compound to adjust the pH of the composition, wherein the pH of the composition is from about 6 to about 9;

movably contacting the substrate face with a pad exerting ~~a between about 0.1 and about 9 psi pressure on the substrate and with the composition under conditions that tungsten is removed both at a rate equal to or greater than 500 Angstroms/minute and at a rate different than the removal of the dielectric material.~~

10. (Currently Amended) A method for chemical mechanical polishing of tungsten comprising:

providing a semiconductor substrate comprising on one face tungsten and a dielectric material;

providing a chemical mechanical polishing composition comprising between about 0.5% and about 10% periodic acid, between about 0.1% and about 10% of malonic acid, and a pH adjusting compound to adjust the pH of the composition, wherein the pH of the composition is between about 4 to about 12 ~~6 to about 9~~; and

movably contacting the substrate face with a pad exerting ~~between about 0.1 and about 9 psi pressure on the substrate and with the composition under conditions that tungsten is removed at a rate different than the removal of the dielectric material.~~